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[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,
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(71) Applicant (for all designated States except US): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventor; and

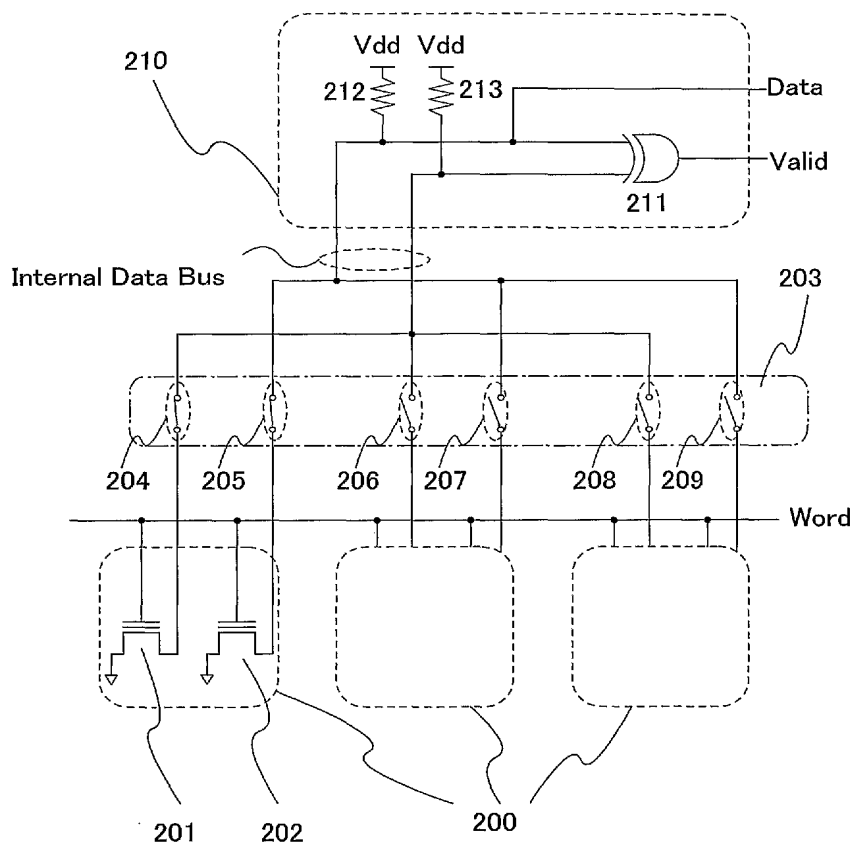
(75) Inventor/Applicant (for US only): **KATO, Kiyoshi**

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(54) Title: NONVOLATILE MEMORY



(57) Abstract: A memory cell for storing 1-bit data is formed by using at least two memory elements in the OTP type nonvolatile memory using a memory element that have two states and can transit only in one direction. In the OTP type nonvolatile memory using a memory element that has two states of an H state (a first state) and an L (a second state) state (hereinafter simply referred to as H and L) and can electrically transit only in one direction from L to H, a memory cell for storing 1-bit data is formed by using two or more memory elements.

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